JANHCF1N5802, JANHCF1N5804, JANHCF1N5806 JANKCF1N5802, JANKCF1N5804, JANKCF1N5806 JANHCH1N5802, JANHCH1N5804, JANHCH1N5806 JANKCH1N5802, JANKCH1N5804, JANKCH1N5806

**ULTRAFAST RECOVERY SILICON RECTIFIER DIE** 

TECHNICAL DATA DATA SHEET 5498, REV A

# **ULTRA FAST RECOVERY SILICON RECTIFIER DIE**

### **FEATURES / BENEFITS:**

- ✓ Die fabricated on a MIL-PRF-19500 JANKC qualified manufacturing line
- ✓ Class H and class K element evaluation per MIL-PRF-19500/477
- ✓ All ratings are @ T<sub>A</sub> = 25 °C unless otherwise specified

# **ELECTRICAL CHARACTERISTICS:**

**Maximum Ratings:** 

Characteristics	Symbol	Condition	Min.	Max.	Units
Peak Inverse Voltage					
DC Blocking Voltage 1N5802	$V_{RWM}$			50	
1N5804		-		100	V
1N5806				150	
Breakdown Voltage					
1N5802	$V_{BR1}$	I <sub>BR</sub> =100μA	60		
1N5804	VDKI	IBR=100µA	110		V
1N5806			160		
Max. Average Forward Current	$I_{F(AV)}$	T <sub>A</sub> = 55°C		1.0	Α
Max. Peak One Cycle Non-	I <sub>FSM</sub>	T <sub>p</sub> = 8.3 ms		35	Α
Repetitive Surge Current		1 p= 0.5 ms			
Max. Junction Temperature	TJ	-	-65	+175	°C
Max. Storage Temperature	$T_{stg}$	-	-65	+175	°C

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	1A, pulse, T <sub>J</sub> = 25 °C	0.875	V
	$V_{F2}$	2.5A, pulse, T <sub>J</sub> = 25 °C	0.975	V
	V <sub>F3</sub>	1A, pulse, T <sub>J</sub> = 125 °C	0.800	V
	$V_{F4}$	1A, pulse, T <sub>J</sub> = -65 °C	1.075	V
Max. Reverse Current	I <sub>R1</sub>	V <sub>R</sub> = V <sub>RWM</sub> , pulse, T <sub>J</sub> = 25 °C	1.0	μΑ
	I <sub>R2</sub>	V <sub>R</sub> = V <sub>RWM</sub> , pulse, T <sub>J</sub> = 125 °C	175	μΑ
Breakdown Voltage 1N5802 1N5804 1N5806	V <sub>BR2</sub>	I <sub>BR</sub> =100μA, T <sub>J</sub> = -65 °C	50 100 150	V
Reverse Recovery Time	t <sub>rr</sub>	$I_F = I_R = 0.5A$ , $I_{RM} = 0.05A$	25	ns
Max. Junction Capacitance C <sub>T</sub>		$V_R = 10V$ , $T_C = 25$ °C $f_{SIG} = 1MHz$ , $V_{SIG} = 50mV$ (p-p)	25	pF

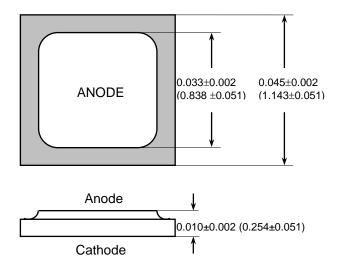
# SENSITRON SEMICONDUCTOR

JANHCF1N5802, JANHCF1N5804, JANHCF1N5806 JANKCF1N5802, JANKCF1N5804, JANKCF1N5806 JANHCH1N5802, JANHCH1N5804, JANHCH1N5806 JANKCH1N5802, JANKCH1N5804, JANKCH1N5806

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# PACKAGE DIMENSIONS (inches/mm):



# **JANHCF/ JANKCF Series**

Top anode and bottom cathode

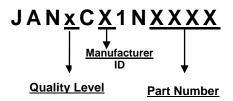
Top Metal Ti (0.3 kA) / Al (45 kA) nominal Bottom Metal Ti (1.2 kA) / Ni (1.8 kA) / Au (4.0 kA) nominal

# **JANHCH/ JANKCH Series**

Top anode and bottom cathode

Top Metal Ti (0.3 kA) / Al (45 kA) nominal Bottom Metal Ti (1.2 kA) / Ni (1.8 kA) / Ag (3.0 kA) nominal

### PART ORDERING INFORMATION:



Suffix	Part Number	Description
Н	JANHCF1N5806	Class H Level
K	JANKCF1N5806	Class K Level

# SENSITRON SEMICONDUCTOR

JANHCF1N5802, JANHCF1N5804, JANHCF1N5806 JANKCF1N5802, JANKCF1N5804, JANKCF1N5806 JANHCH1N5802, JANHCH1N5804, JANHCH1N5806 JANKCH1N5802, JANKCH1N5804, JANKCH1N5806

**ULTRAFAST RECOVERY SILICON RECTIFIER DIE** 

# TECHNICAL DATA DATA SHEET 5498, REV A

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